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(54) **USING A FIELD EFFECT DEVICE FOR IDENTIFYING TRANSLOCATING CHARGE-TAGGED MOLECULES IN A NANOPORE SEQUENCING DEVICE**

(2013.01); **H01L 51/055** (2013.01); **H01L 51/0558** (2013.01); **G01N 33/18** (2013.01)

(58) **Field of Classification Search**

None

See application file for complete search history.

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(60) Provisional application No. 61/536,327, filed on Sep. 19, 2011, provisional application No. 61/536,381, filed on Sep. 19, 2011.

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(Continued)

(57) **ABSTRACT**

A detector apparatus includes a field-effect transistor configured to undergo a change in amplitude of a source-to-drain current when at least a portion of a charge-tagged molecule translocates through the nanopore. In some implementations, the field-effect transistor is a carbon nanotube field effect transistor and the nanopore is located in a membrane. In other implementations, the field-effect transistor is a carbon nanotube field effect transistor and the nanopore is implemented in the form of a nano-channel in a semiconductor layer.

(52) **U.S. Cl.**

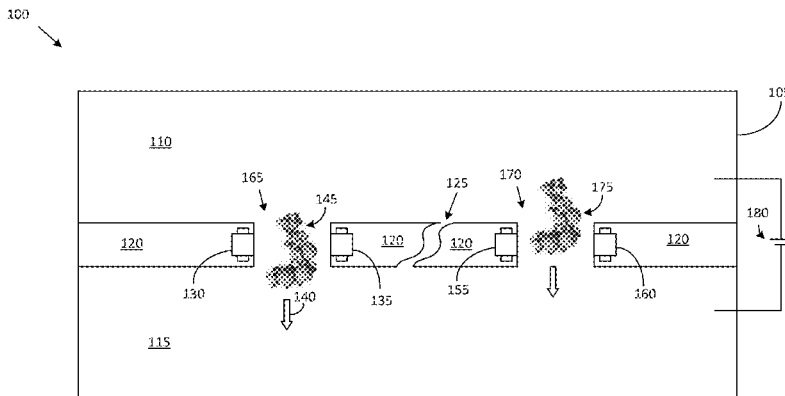
CPC ..... **G01N 33/48721** (2013.01); **B82Y 15/00**

(2013.01); **C12Q 1/6869** (2013.01); **G01N**

**27/4145** (2013.01); **G01N 27/44704** (2013.01);

**G01N 33/1826** (2013.01); **H01L 51/0048**

**6 Claims, 8 Drawing Sheets**



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*C12Q 1/68* (2006.01)  
*G01N 27/447* (2006.01)  
*G01N 33/18* (2006.01)

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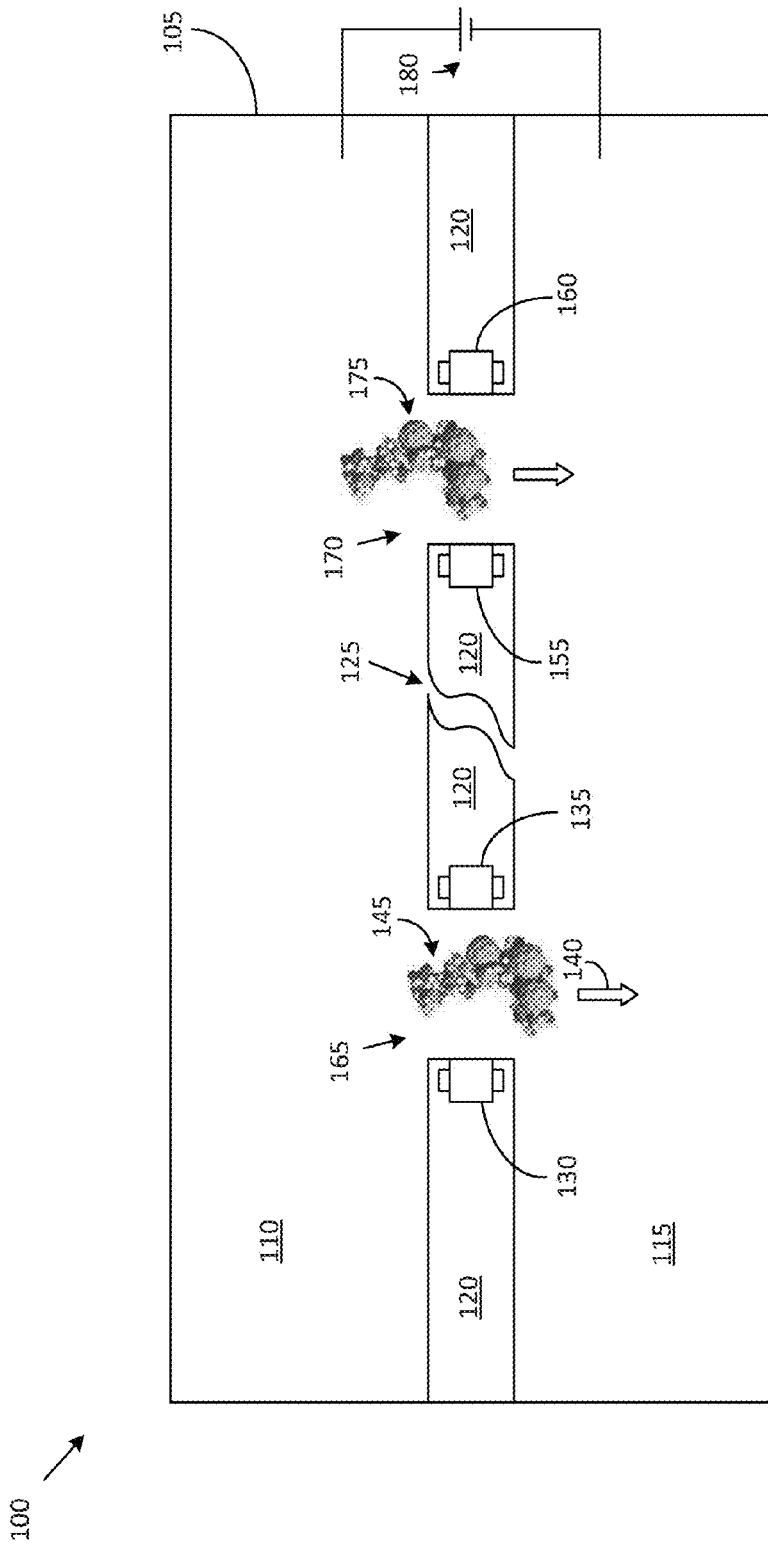


FIG. 1

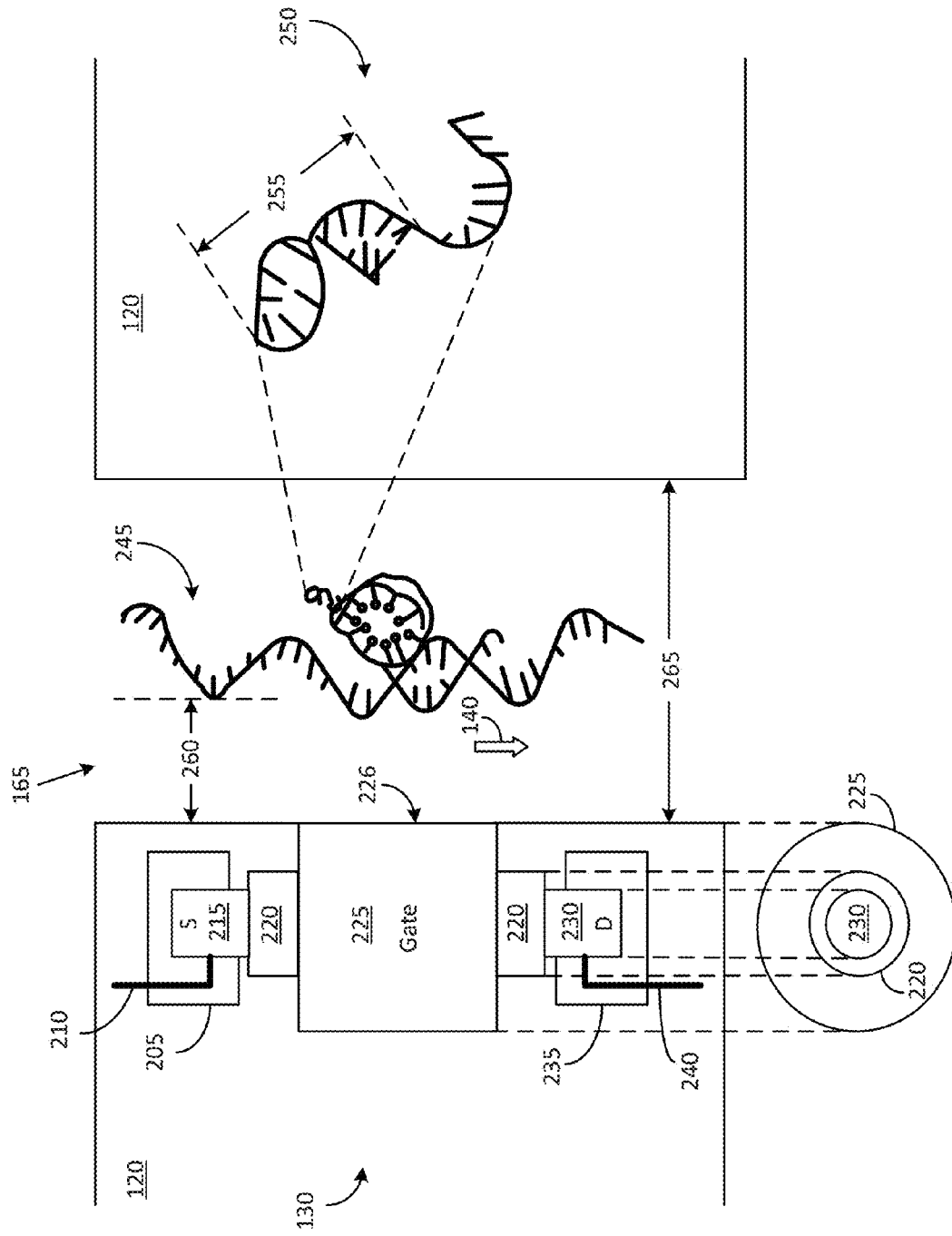


FIG. 2

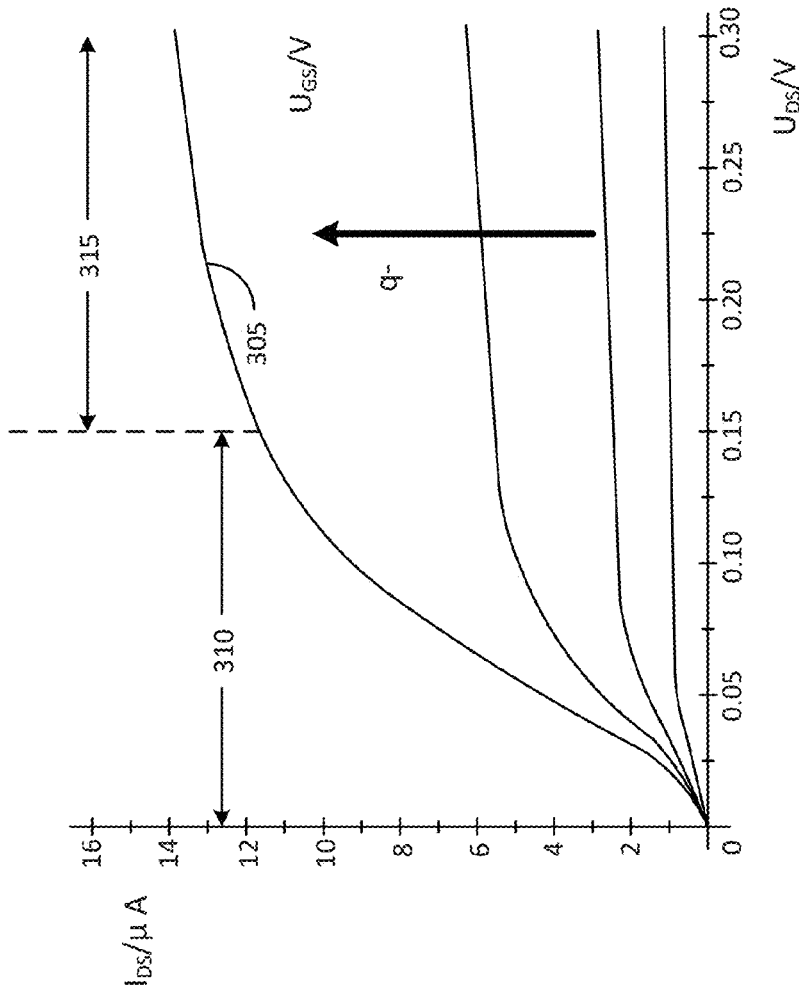


FIG. 3

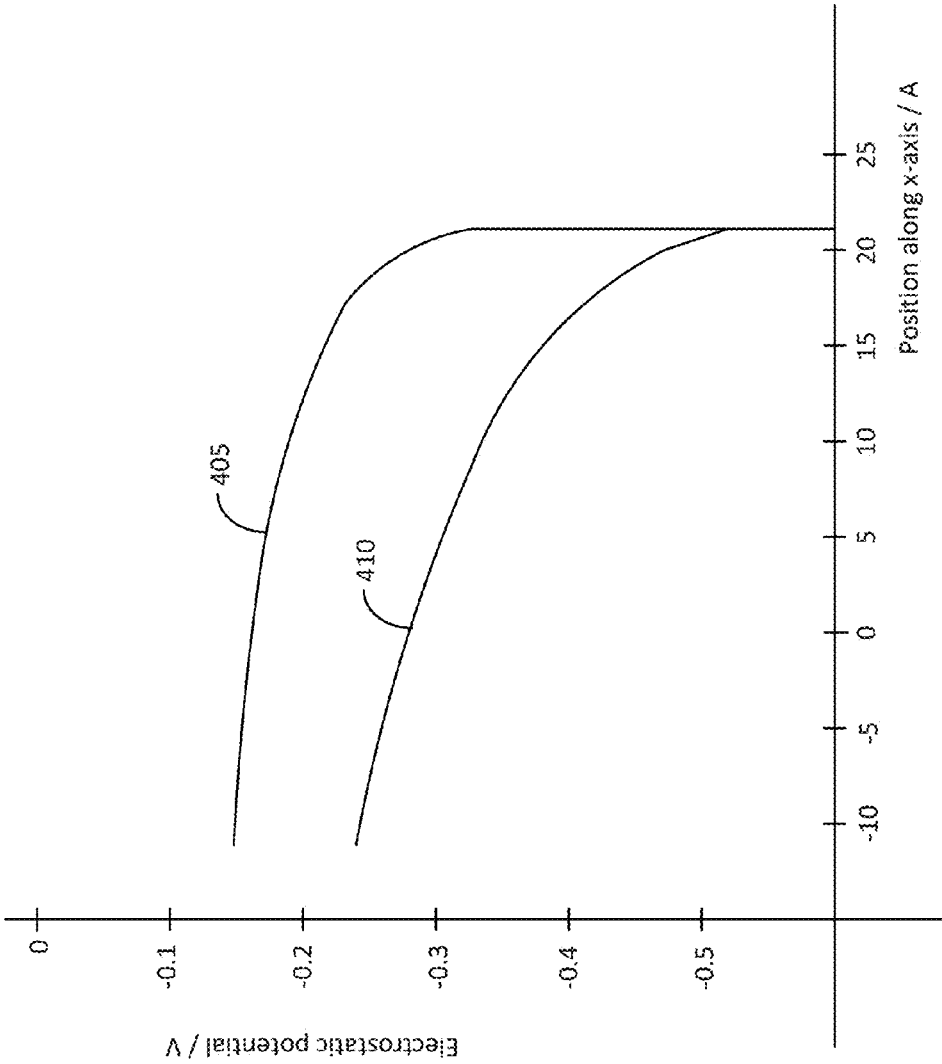


FIG. 4

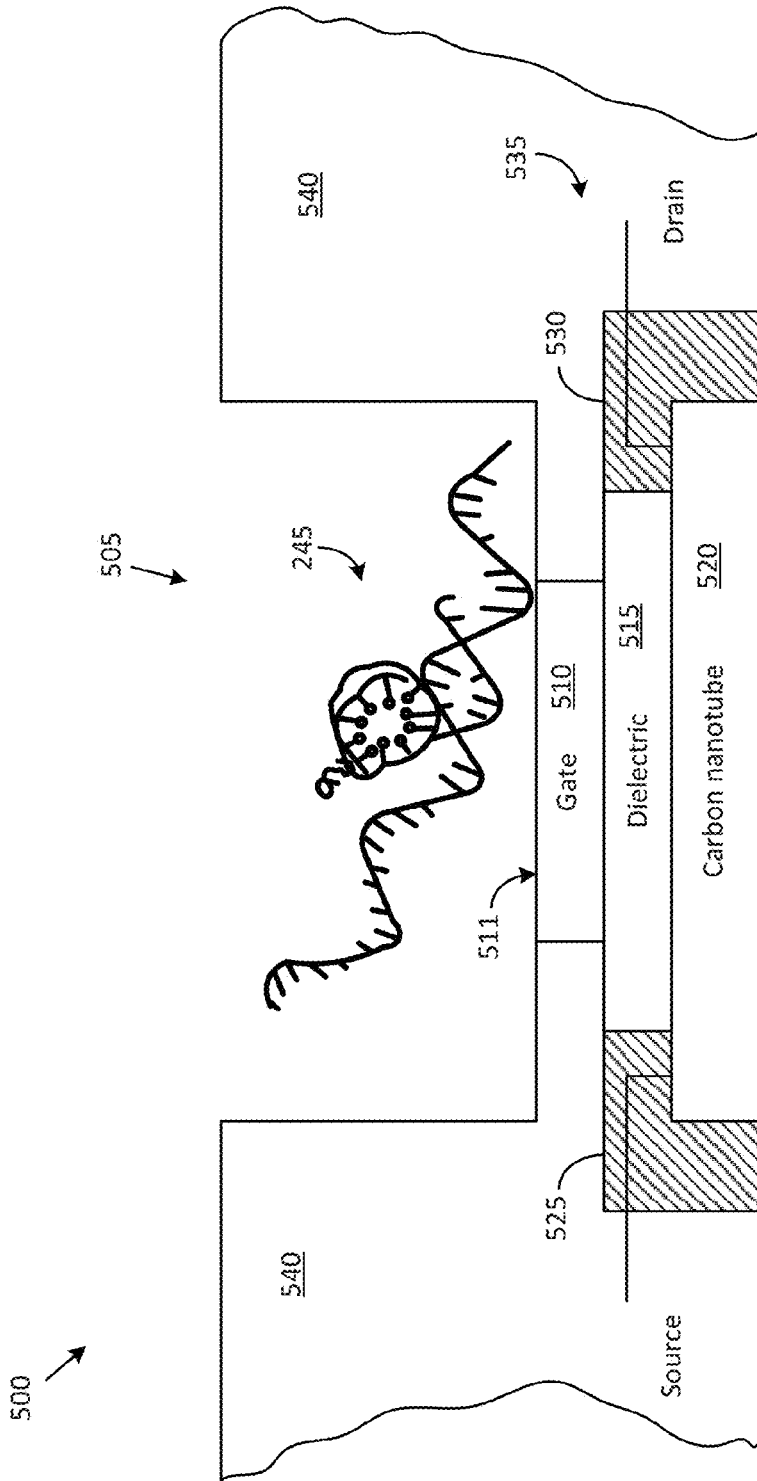


FIG. 5

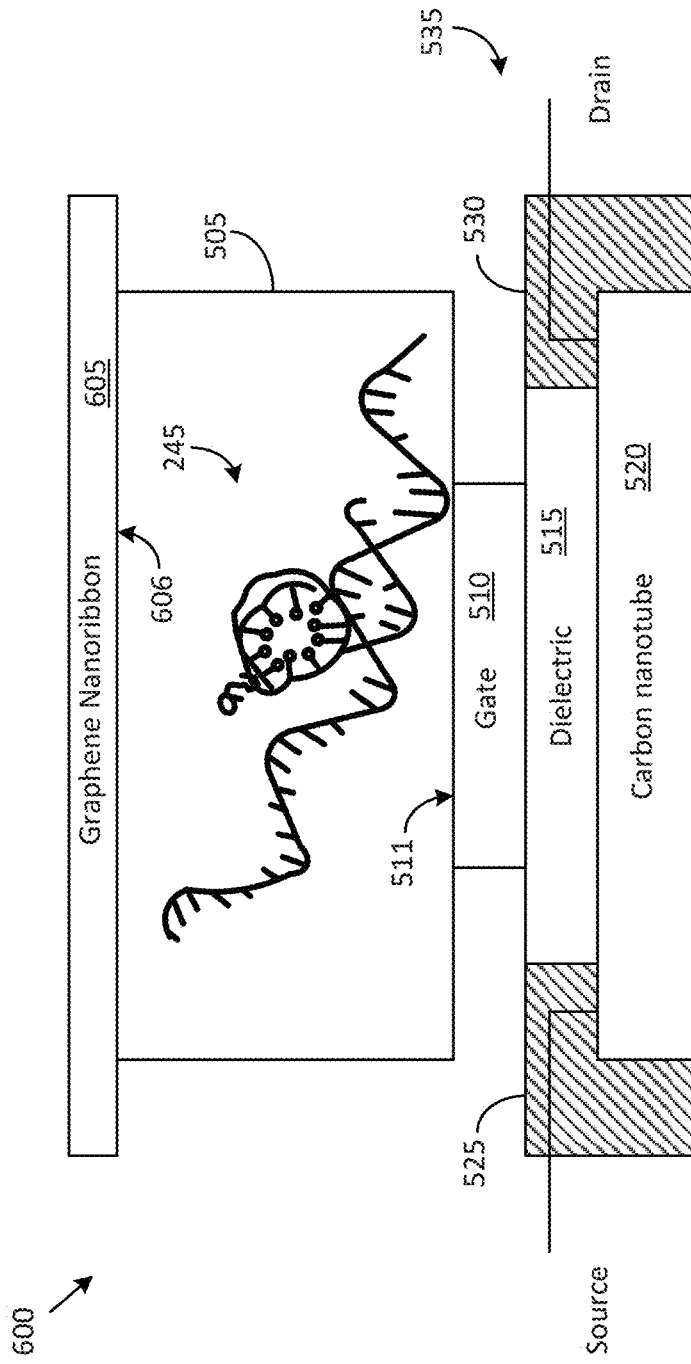


FIG. 6



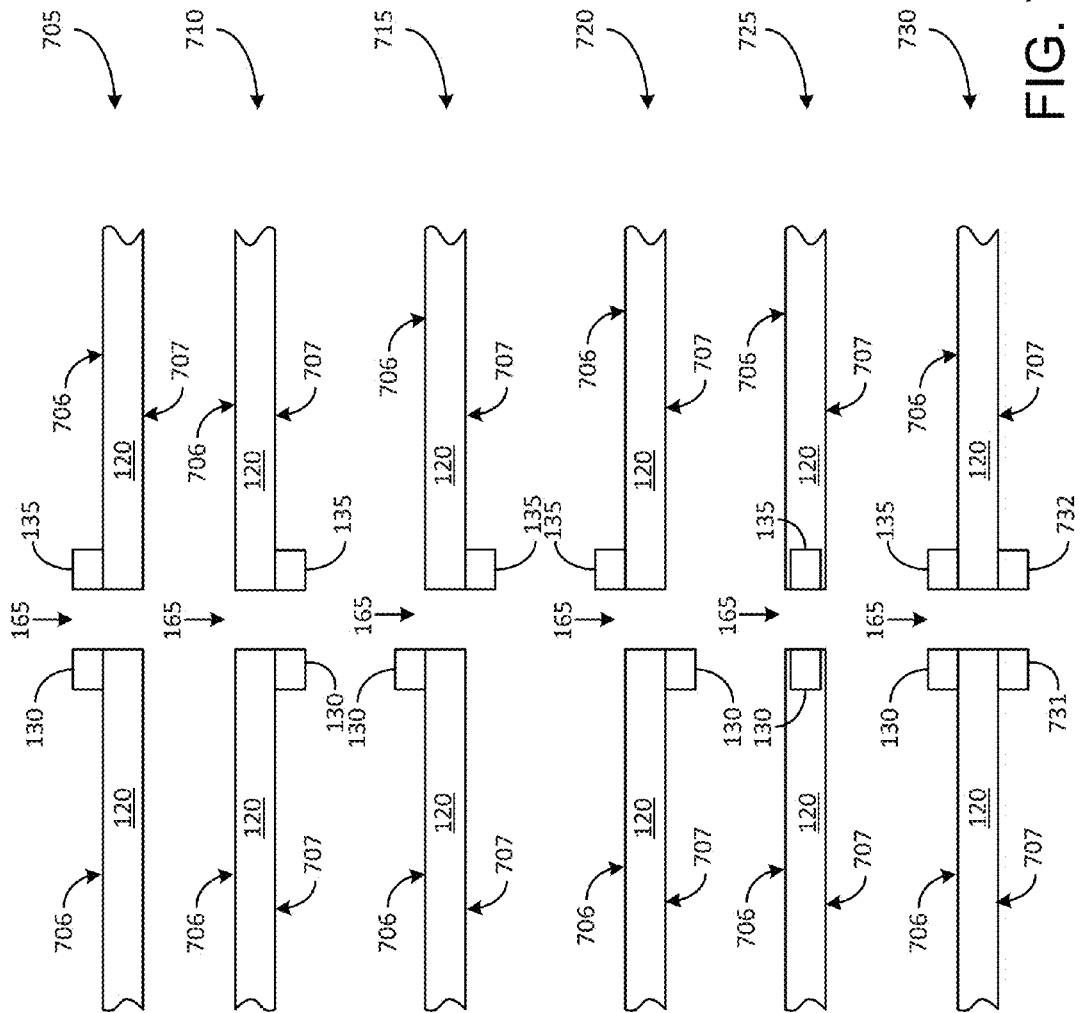


FIG. 7

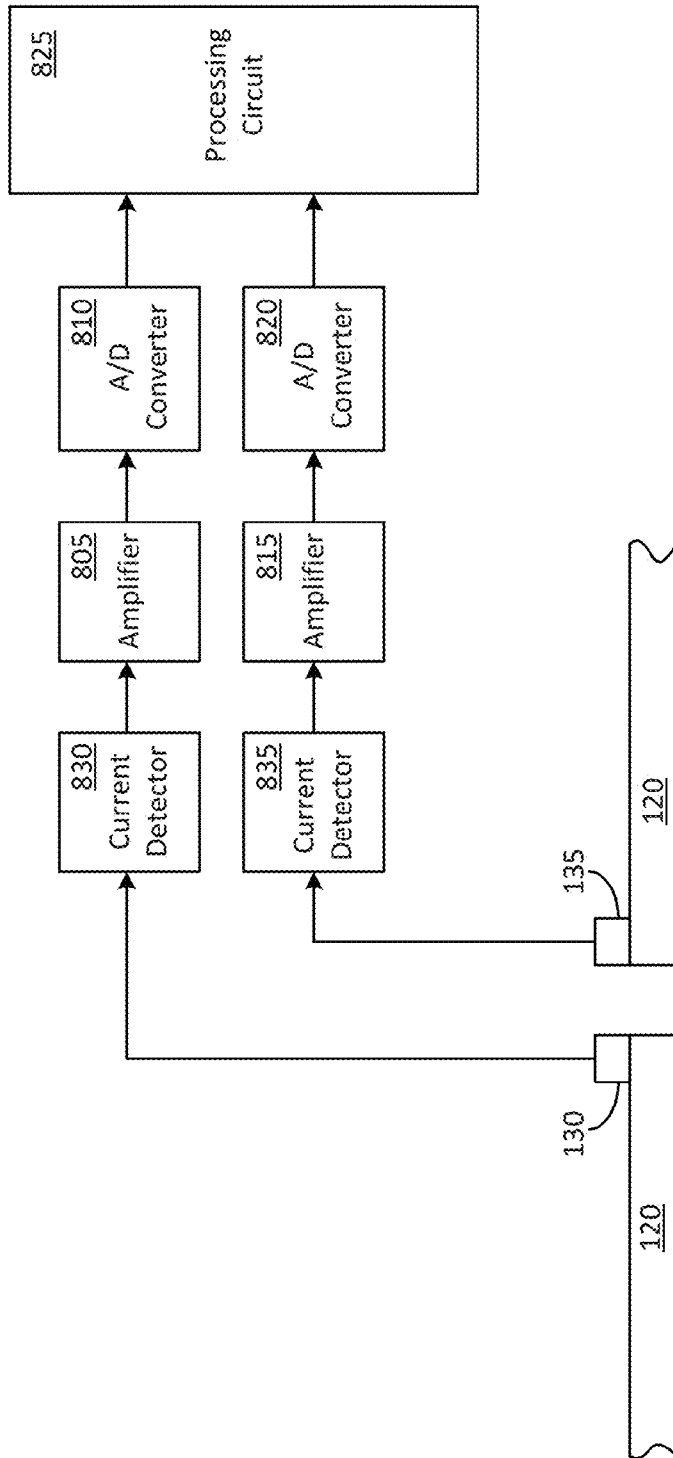


FIG. 8

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## USING A FIELD EFFECT DEVICE FOR IDENTIFYING TRANSLOCATING CHARGE-TAGGED MOLECULES IN A NANOPORE SEQUENCING DEVICE

### CROSS REFERENCE TO RELATED APPLICATIONS

The present application is a Divisional of U.S. application Ser. No. 13/621,745 filed on Sep. 17, 2012, which in turn claims priority to U.S. Provisional Application 61/536,327 filed on Sep. 19, 2011, entitled "ssDNA Translocation Control and Nucleotide Sequencing Nano-Device Mechanisms" and U.S. Provisional Application 61/536,381 filed on Sep. 19, 2011, entitled "ssDNA Translocation Control and Nucleotide Sequencing Nano-Device Mechanisms", all of which are incorporated herein by reference in their entirety. The present application is also related to U.S. patent application Ser. No. 13/621,735 filed on Sep. 17, 2012, entitled "Translocation and Nucleotide Reading Mechanisms for Sequencing Nanodevices", and U.S. patent application Ser. No. 14/576,148 filed on Dec. 18, 2014, entitled "Translocation and Nucleotide Reading Mechanisms for Sequencing Nanodevices", which are also incorporated herein by reference in their entirety.

### FIELD

The present teachings relate to detection devices that may be used in connection with charge-tagged molecules translocating through a nanopore. More specifically, the present disclosure relates to detection devices that can be used for identification of nucleic acid sequences in charge-tagged DNA/RNA molecules.

### BACKGROUND

Inexpensive and time-efficient full genome sequencing will enable prediction and impact-minimization of diseases through personalized, preventive medicine. Full genome sequencing is clearly of great importance for research into the basis of genetic disease. For example, access to a large database of individualized genome sequences will facilitate cross-correlating gene-type to gene-function.

However, full-genome sequencing with current technologies (e.g. chemical- or enzymatic-based shot-gun DNA sequencing, including massively parallel automated sequencers based on slab gel separation or capillary electrophoresis) is inadequate both in terms of performance and also in terms of cost.

### SUMMARY

According to a first aspect of the present disclosure, a detector apparatus includes a membrane and a first field effect transistor. The membrane contains a nanopore and the first field-effect transistor is configured to undergo a change in amplitude of a source-to-drain current when at least a portion of a charge-tagged molecule translocates through the nanopore.

According to a second aspect of the present disclosure, a detector apparatus includes a field-effect transistor and a solid-state membrane. The field-effect transistor has a planar gate terminal, and the semiconductor layer has a nano-channel with a first portion of the nano-channel abutting a major surface of the planar gate terminal.

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According to a third aspect of the present disclosure, a method of detection includes: a) forming a charge-tagged molecule, b) propagating the charge-tagged molecule through a nanopore of a membrane, and c) detecting a first amplitude of a source-to-drain current in a first field effect transistor, the first amplitude indicative of at least one charge tag in the charge-tagged molecule modifying an electrostatic potential of a gate portion of the first field-effect transistor.

Further aspects of the disclosure are shown in the specification, drawings and claims of the present application.

### BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are incorporated into and constitute a part of this specification, illustrate one or more embodiments of the present disclosure and, together with the description of a few example embodiments, serve to explain the principles and implementations of the disclosure. The components in the drawings are not necessarily drawn to scale. Instead, emphasis is placed upon clearly illustrating various principles. Moreover, in the drawings, like reference numerals designate corresponding parts throughout the several views.

FIG. 1 shows a detection apparatus for detecting charge-tagged DNA molecules propagating through nanopores of a membrane in accordance with a first embodiment of the present disclosure.

FIG. 2 shows some details of a carbon nanotube FET (CNTFET) that is a part of the detection apparatus in accordance with the present disclosure.

FIG. 3 shows the effect of changes in charge-tag magnitudes on a drain-to-source current-voltage (I-V) characteristic graph of a CNTFET in accordance with the present disclosure.

FIG. 4 shows a graph of electrostatic potential with and without the charge tag contribution from a 10-base charge-tagged ssDNA oligomer at various distances from a gate portion of a CNTFET.

FIG. 5 shows a detection apparatus for detecting charge-tagged DNA molecules propagating through a nanopore in accordance with a second embodiment of the present disclosure.

FIG. 6 shows a detection apparatus for detecting charge-tagged DNA molecules propagating through a nanopore in accordance with a third embodiment of the present disclosure.

FIG. 7 shows various configurations for mounting a pair of CNTFETs upon a membrane in accordance with the present disclosure.

FIG. 8 shows additional elements that are coupled to a pair of CNTFETs for carrying out various types of processing operations upon data provided by the pair of CNTFETs.

### DETAILED DESCRIPTION

Throughout this description, embodiments and variations are described for the purpose of illustrating uses and implementations of the inventive concept. The illustrative description should be understood as presenting examples of the inventive concept, rather than as limiting the scope of the concept as disclosed herein.

The various embodiments described herein are generally directed at using realizable solid-state membranes, more specifically realizable silicon nitride semiconductor membranes having nanopores. One or more field effect transistors (FETs) are located near one or more nanopores and the FETs

are used to detect charge-tagged molecules that are propagated through the nanopores by using an ionic current.

The FETs used for this purpose are sized and structured differently from conventional FETs. More specifically, the source-to-drain current ( $I_{DS}$  current) in a conventional FET is typically controlled by changing the dimension of a conducting channel located between the source and drain terminals. This change in dimension is carried out by applying a voltage to a gate region of the FET via a gate terminal provided in the form of a metal contact. As can be understood, the size of the conducting channel is proportional to the length and the width of the gate region. The width may be selected to be much larger than the length, in order to provide amplification of a signal applied to the source terminal of the device. Furthermore, while the width limits the current carrying capacity and electrostatics sensitivity of the device, the length of the gate region limits the upper switching frequency of the device.

In contrast to the sizing and structure of a conventional FET, the FETs used in accordance with the present disclosure are miniature sized devices achieved by using carbon nanotubes (CNTs).

Carbon nanotube FETs (CNTFETs) have been built and demonstrated by various entities. For example, attention is drawn to a paper by Wind et al (reference [5]), which describes a CNTFET incorporating top gate electrodes. However, a CNTFET adapted for various embodiments in accordance with this present disclosure contains a modified gate region. More specifically, a CNTFET in accordance with the present disclosure is structured such that the source-drain current ( $I_{DS}$  current) is controlled by charges present external to the CNTFET in the vicinity of the gate region, thereby dispensing with the conventional gate terminal (metal contact for providing the gate voltage). The structural basis and use of this CNTFET in accordance with the present disclosure will be described below in more detail using the various figures.

Attention is first drawn to FIG. 1, which shows a detection apparatus **105**, which may be alternatively referred to herein as a nanopore sequencing device, for detecting charge-tagged molecules propagating through nanopores **165** and **170** of a membrane **120** in accordance with a first example embodiment of the present disclosure. Detection apparatus **105** contains an upper reservoir **110** and a lower reservoir **115** with a membrane **120** disposed between the two reservoirs. Membrane **120** contains several nanopores (only two of which are shown in FIG. 1 for convenience). Reservoirs **110** and **115** contain a solution, such as for example, a mixture of water and potassium chloride (KCl), which is conducive to generating an ionic current upon application of a suitable voltage via a voltage source **180**.

When the ionic current is generated, charge-tagged species, such as charge-tagged DNA molecules **145** and **175**, propagate through nanopores **165** and **170** respectively of the nanopore sequencing device.

Charge-tagged DNA molecules can be generated in a variety of ways. For example, oligonucleotide charge-tags may be implemented via solid-phase synthesis using a phosphoramidite method (as disclosed in reference [4]) and phosphoramidite building blocks derived from protected 2'-deoxynucleosides (dA, dC, dG, and T), ribonucleosides (A, C, G, and U), or chemically modified nucleosides. Oligonucleotides between 16-28 bases long may be obtained by sequentially coupling the building blocks to the growing oligonucleotide chain in the order required by the sequence of the product. In accordance with various embodiments of the present disclosure, only the net charge of the oligonucle-

otide is used. Consequently, it is desirable to minimize the radius of gyration and choose a sequence based on partial complementarity along the chain so as to enable formation of looped structures with one exposed end having a minimum of 3-4 bases free for stable binding to a single-strand DNA (ssDNA) backbone. Having 3-4 bases free translates to a total of 64-256 different oligonucleotide combinations. The product of the solid-state synthesis is then released from the solid phase to a ssDNA solution, deprotected, and collected. The prepared oligonucleotides diffusively bind in solution to complementary codons in the ssDNA/RNA to form the charge tags.

Turning now to nanopores **165** and **170** contained in membrane **120**, it may be pertinent to point out that only nanopore **165** and associated elements have been referred to in the description below. However, it should be understood, that the description is equally applicable to other similar nanopores and associated elements. (In this context, attention is drawn to jagged break **125** that is indicative of membrane **120** containing a larger area and more nanopores).

Nanopore **165** is populated with two CNTFETs **130** and **135** that are shown located inside membrane **120** and diametrically opposed to each other with respect to nanopore **165**. Each of the two CNTFETs **130** and **135** operate as low dielectric constant FETs in a solvated environment (ionic solution).

A substantial portion of the gate of each of CNTFETs **130** and **135** is oriented parallel to a direction of flow of molecule **145** (indicated by arrow **140**) and exposed to the nano channel. The amplitude of a source-to-drain current ( $I_{DS}$  current) flowing in each of the two devices is modified when molecule **145** is located in proximity to the gate portions. In one embodiment, the  $I_{DS}$  current increases when the tagged-charge present in molecule **145** is proximally located to the gate region of either CNTFET. Further details pertaining to detection apparatus **105** will be provided using other figures.

FIG. 2 shows additional details of CNTFET **130** that is shown in FIG. 1. It will be understood that in certain applications such as the one shown in FIG. 2, a single CNTFET **130**, will be used, whereas in other applications CNTFET **130** will be used in conjunction with one or more additional CNTFETs such as CNTFET **135** shown in FIG. 1. The use of multiple CNTFETs provides various advantages such as, for example, increased detection sensitivity, redundant operation, and error checking features.

CNTFET **130** includes a gate portion **225** having a major surface **226** arranged in parallel to the direction of propagation **140** of a charge-tagged molecule, which in this example, is a charge-tagged single-strand DNA (ssDNA) molecule **245**. In other implementations, the charge-tagged molecule may be other molecules, such as for example, charge-tagged RNA molecules. The charge-tagged ssDNA molecule **245** has a 3 to 4 base oligomer-ssDNA complementarity that provides thermodynamic stability to the complex, particularly using locked nucleic acid (LNAs as described in references [6] and [7]) oligomers. Oligonucleotide **250** includes a hairpin length **255** that determines the charge.

Gate portion **225** comprises a dielectric material such as a polysilicon, which is wrapped around a carbon nanotube portion **220**. The CNTFET **130** further includes a source portion **215**, a source pad **205**, a drain portion **230**, and a drain pad **235**. Source-to-drain biasing may be provided by applying a  $U_{DS}$  voltage (not shown) via terminals **210** and **240** that are connected to source portion **215** and drain portion **230** respectively. The  $U_{DS}$  voltage sets up a quies-

cent current flow between the source and drain portions. This quiescent current is modified in amplitude when charge-tagged single-strand DNA (ssDNA) **245** is in proximity to gate portion **225** when propagating through nanopore **165**.

The proximity parameter is determined in part by selecting a suitable diameter **265** of the nanopore **165**. In one example embodiment, diameter **265** is selected not to exceed 3 nm. Diameter **265** may be alternatively viewed as a contributory factor for a separation distance **260** between major surface **226** and charge-tagged single-strand DNA (ssDNA) **245** that is translocating through nanopore **165**. In one example embodiment, separation distance **260** is about 2 nm.

The fabrication of CNTFET **130** may be carried out via a number of techniques. In one approach, semiconducting single-walled carbon nanotubes are used because such devices provide certain advantages (such as faster switching properties at low source/drain voltages) over metallic single-walled and metallic multi-walled tubes. The silicon-based fabrication of nanopores may be carried out via processes such as described in reference [1]. The fabrication process described in reference [1] may be modified to include additional steps that include incorporating CNTFET **130** within or outside membrane **120**.

In general, the fabrication process may begin with building a wrap-around CNTFET (preferred over top-gated devices like the one disclosed in reference [5]) since the wrap-around CNTFET provides an improved device on/off ratio. The wrapping is carried out using a dielectric material that is wrapped around the entire length of the CNTFET. The CNTFET is then placed upon membrane **120** and a portion of the wrapping is removed (for example, by etching) so as to expose the extremities of carbon nanotube portion **220**. Source, drain, and gate contacts may then be provided. A focused electron beam may be used to create one or more 2-3 nm nanopores in membrane **120**. The nanopore fabrication process may be carried out as disclosed in reference [1]. Then one or more CNTFETs are incorporated into or on membrane **120**. In the FIG. 1 embodiment, the nanopore is created between the two CNTFETs.

Attention is now drawn to FIG. 3, which shows the effect of changes in charge-tag magnitudes on a drain-to-source current-voltage (I-V) characteristic of a CNTFET in accordance with the present disclosure. Each of the curves represent gate-to-source voltages ( $U_{GS}$ ) corresponding to various gate charges ( $q$ ). Using curve **305** for purposes of explanation, it can be observed that curve **305** includes a substantially linear rising portion **310** (where  $I_{DS}$  rises substantially linearly in correspondence to an increase in  $U_{DS}$  the drain-to-source voltage); and a substantially flat portion **315** (where the  $I_{DS}$  remains substantially constant upon increase in  $U_{DS}$ ). The linear rising portion **310** corresponds to a linear mode of operation of detection apparatus **105** and it is this linear mode of operation that is used in the various embodiments in accordance with the present disclosure. The substantially flat portion **315**, which corresponds to a saturated region of operation, is not typically used when identifying translocating charge-tagged molecules.

The linear mode of operation is used so as to enable identification and detection of the 64-256 different free end oligonucleotide combinations that correspond to the 3-4 bases which are free to bind stably to a backbone complementary sequence of bases of a ssDNA molecule. Each of the 64-256 combinations generates a uniquely identifiable change in  $I_{DS}$  current in a CNTFET. In contrast, the saturated mode of operation would be unsuitable for use in detecting

these various combinations because  $I_{DS}$  would remain relatively constant for the various combinations. However, the saturated region of operation may be utilized in various other applications in accordance with the disclosure that support a CNTFET on-off switching mode of operation.

FIG. 4 shows a graph of electrostatic potential versus charge tag contribution from a 10-base oligomer charge-tagged ssDNA at various distances ("r") from a CNTFET gate.

Curve **410** indicates the total electrostatic potential without a charge-tag and curve **405** indicates the changed electrostatic potential due to the presence of a 10-base oligonucleotide charge-tag as a function of varying distances (r) from a CNTFET gate. At  $r=1$  nm the charge tag is a few tenths of a Volt, sufficient to activate  $I_{DS}$  current change in the CNTFET.

A predictive simulation involving a Non-Equilibrium Green's Function (NEGF) approach was used to compute the current-voltage (IV) and device conductance graph shown in FIG. 4. Carbon atoms were described using an extended Huckel model (as disclosed in reference [2]) with Cerda basis (reference [3]). For a 1.8 nm gate: a  $V_{GD}=-0.4V$  increases the nanotube resistance from 22.13-22.14 k $\Omega$ , and for a 0.9 nm gate  $V_{GD}=-0.4V$  increases nanotube resistance from 22.14-22.20 k $\Omega$ . Larger gating effect would lead to higher nucleic acid distinguishability in a nucleobase sequencing nanopore device.

In one quantum mechanical simulation using an explicit solvent model, charge-screening effects on the gate potential were predicted using short (~10 bases long) 3-base complementary oligomeric charge tags on specific ssDNA sequences. In this predictive quantum mechanical calculation, the detector apparatus remains operational within  $r<=1$  nm, and provides discriminatory electron current signatures  $I_{SD}$  for different nucleic acid sequences with charge-tags differing by 2-4e.

FIG. 5 shows a detection apparatus **500** for detecting charge-tagged DNA molecules propagating through a nanopore in accordance with a second embodiment of the present disclosure. In this embodiment, CNTFET **535** has a planar configuration that may be fabricated using semiconductor fabrication techniques. CNTFET **535** includes a carbon nanotube portion **520**, a dielectric portion **515**, a source portion **525**, a drain portion **530**, and a gate portion **510** having a major surface **511** abutting a channel **505**. Channel **505** is representative of a nanopore through which a charge-tagged molecule, such as charge-tagged single-strand DNA (ssDNA) **245**, is translocated using an ionic solution. Channel **505** may be fabricated in the form of a groove in a semiconductor layer **540**, with a longitudinal axis of the groove projecting out of the plane of the paper on which FIG. 5 is drawn. It will therefore be understood that charge-tagged single-strand DNA (ssDNA) **245** translocates along this longitudinal axis, or in other words in a direction that may be viewed as emerging out of the drawing sheet on which FIG. 5 is drawn.

Furthermore, it will be understood that though channel **505** is shown in FIG. 5 as having a rectangular cross-section, various other cross-sectional configurations such as a circular cross-section, may be used instead. Generally, the cross-section is selected so as to provide an interaction region with gate **510** whereby a charge-tagged molecule propagating through the nanopore has an effect on the  $I_{DS}$  current flow in CNTFET **535**.

In a sixth configuration **730**, four CNT FETs are used. Specifically, a first CNTFET **130** and a second CNTFET **731** are each located on opposing major surfaces **706** and **707** on

one side of nanopore 165. A third CNTFET 135 and a fourth CNTFET 732 are each located on opposing major surfaces 706 and 707 on a diametrically opposite side of nanopore 165.

In contrast, to the embodiment shown in FIG. 5 (wherein CNTFET 535 is used as a single detector for identifying charge-tagged molecules propagating through a nanopore), the third embodiment of a detector apparatus 600 shown in FIG. 6 incorporates two detectors.

The first detector is a CNTFET 535 that has been described above. The second detector is implemented in the form of a graphene nanoribbon layer 605 that abuts an opposing surface 606 of channel 505. Opposing surface 606 opposes major surface 511 described above. A quiescent current may be generated across the graphene nanoribbon 605 upon application of a suitable biasing voltage between the two ends laid on top of the silicon support 605 by using a suitable voltage source (not shown). This quiescent current is affected when a charge-tagged molecule propagates through nanopore 505. The change in current, which may be referred to herein as a sense current, is used to detect the various free end oligonucleotide combinations that may be present in a backbone of a charge-tagged ssDNA molecule propagating through nanopore 505.

FIG. 7 shows various configurations for mounting a pair of CNTFETs upon a membrane in accordance with the present disclosure. In a first configuration 705, a first CNTFET 130 is located upon a first major surface 706 of membrane 120 on one side of nanopore 165. A second CNTFET 135 is located upon the same first major surface 706 of membrane 120 but on a diametrically opposite side of nanopore 165.

In a second configuration 710, the first CNTFET 130 is located upon an opposing major surface 707 of membrane 120 on one side of nanopore 165. A second CNTFET 135 is located upon the same opposing major surface 707 of membrane 120 but on a diametrically opposite side of nanopore 165.

In a third configuration 715, the first CNTFET 130 is located upon a first major surface 706 of membrane 120 on one side of nanopore 165. A second CNTFET 135 is located upon the opposing major surface 707 of membrane 120 on a diametrically opposite side of nanopore 165.

In a fourth configuration 720, the second CNTFET 135 is located upon a first major surface 706 of membrane 120 on one side of nanopore 165. The first CNTFET 130 is located upon the opposing major surface 707 of membrane 120 on a diametrically opposite side of nanopore 165.

In a fifth configuration 725, one or more CNTFETs may be embedded inside membrane 120. (FIG. 1 shows several CNTFETs embedded in membrane 120). In one embodiment wherein one or more CNTFETs are embedded inside membrane 120, membrane 120 is selected to have a thickness 726 between 20-50 nanometers.

FIG. 8 shows additional elements that are coupled to a pair of CNTFETs for carrying out various types of processing operations upon data provided by the pair of CNTFETs. More particularly, the  $I_{DS}$  currents generated in CNTFETs 130 and 135, which may be a part of current detectors 830 and 835 respectively, are amplified in instrumentation amplifiers 805 and 810 for generating amplified voltage signals. The voltage signals generated in the two amplifiers are provided to a pair of analog-to-digital converters (ADCs) 810 and 820. The digital signals generated by the pair of converters from the amplified voltage signals are provided to processing circuit 825, which processes the digital signals to obtain meaningful information. Processing circuit 825

includes various elements (not shown) such as a processor, a computer-readable storage medium for storing data and/or software/firmware programs, and input/output interface elements.

It will be understood that the digital data provided to processing circuit 825 by ADCs 810 and 820, may be used for implementing various features in accordance with the present disclosure, such as redundant operations, error-correction operations, and/or parallel processing operations. For example, in a redundant mode of operation, a failure in one of the two CNTFETs may be addressed by ignoring the failed CNTFET and using only the one operational CNFT. In an error-correction mode of operation the digital data provided by the two CNTFETs may be compared against each other in order to ensure accuracy and robustness of operation. In parallel processing operations, the  $I_{DS}$  currents generated by two or more CNTFETs 130 and 135 may be used to derive a variety of information pertaining to a single charge-tagged molecule, or multiple charge-tagged molecules that may be concurrently or sequentially propagating through a nanopore.

Furthermore, while FIG. 8, shows CNTFETs 130 and 135 in a detection configuration corresponding to the first embodiment described above, the processing operations and elements described using FIG. 8 are equally valid for various other embodiments (for example, the embodiment shown in FIG. 6) wherein a pair of CNTFETs are employed.

Turning away from FIG. 8, attention is once again drawn to FIG. 2. The interaction between CNTFET 130 and charge-tagged single-strand DNA (ssDNA) 245 may be calculated by assuming a minimized gate capacitance (i.e.  $A$  and  $\epsilon_0\epsilon_r$  in the following equation for gate capacitance:  $C=\epsilon_0\epsilon_r A/r$ , where "r" is the separation distance 260); an estimated Coulomb interaction effect (for example, from water) via expressing the contribution to the E-field at a point in space (CNTFET gate surface) due to a single, discrete point charge ( $ne$ , from charge species) located at another point in space, distanced by  $r$ , results in an electrical potential of  $\geq 0.9V$  for  $r\leq 2$  nm. This calculation also assumes: discrete water molecules in the nanopore have a dielectric constant dominated by their orientation (large dipole moment), stronger screening effects in (K<sup>+</sup>) ionic solution (the negatively charged ssDNA backbone and negative charge-tags attract positive counter ions), and that the complex appears neutral from distance larger than the backbone-counter ion distance (although the nanopore may strip ions from ssDNA backbone during translocation) to determine a worst case scenario for operating the CNTFET device in the linear mode of operation.

A test model comprising a nanotube ( $m=5$ ,  $n=0$ , length=4.3 nm), left and right metallic electrodes, a dielectric region (with dielectric constant 4) separating the nanotube and the gate, and a gate bias voltage was used to assess performance of a modeled embodiment of the present disclosure. The gate size was selected to be approximately 1.2x1.2 nm, which approximates to the electric field of a point charge. Assuming a charge-tag with 20e (i.e. 20 nucleotides long), a small nanopore (1.5-2.5 nm) capable of stripping counter ions from the charge-tag, and a distance of approximately 1 nm between the charge-tag and a CNTFET gate insulator surface leads to a potential at the insulator of -0.4V (screened Coulomb).

In conclusion, a detector apparatus in accordance with the present disclosure enables sufficiently small charge tags (for example, 8-136 bases, considering a 3-base complementary overlap between charge tag and ssDNA) on ssDNA to gate-activate a CNTFET in a linear mode of operation. The

detector apparatus preferably has a device sensitivity that enables detection of small tags with 2-4e potential difference at distances ~1 nm in a solvated environment (ionic solution described above).

All patents and publications mentioned in the specification may be indicative of the levels of skill of those skilled in the art to which the disclosure pertains. All references cited in this disclosure are incorporated by reference to the same extent as if each reference had been incorporated by reference in its entirety individually.

It is to be understood that the disclosure is not limited to particular methods or systems, which can, of course, vary. It is also to be understood that the terminology used herein is for the purpose of describing particular embodiments only, and is not intended to be limiting. As used in this specification and the appended claims, the singular forms "a," "an," and "the" include plural referents unless the content clearly dictates otherwise. The term "plurality" includes two or more referents unless the content clearly dictates otherwise. Unless defined otherwise, all technical and scientific terms used herein have the same meaning as commonly understood by one of ordinary skill in the art to which the disclosure pertains.

The examples set forth above are provided to give those of ordinary skill in the art a complete disclosure and description of how to make and use the embodiments of the terrain traversal device of the disclosure, and are not intended to limit the scope of what the inventors regard as their disclosure. Modifications of the above-described modes for carrying out the disclosure may be used by persons of skill in the robotic arts, and are intended to be within the scope of the following claims.

A number of embodiments of the disclosure have been described. Nevertheless, it will be understood that various modifications may be made without departing from the spirit and scope of the present disclosure. Accordingly, other embodiments are within the scope of the following claims.

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What is claimed is:

1. A detector apparatus comprising:

a field-effect transistor having a planar gate terminal; and a semiconductor layer comprising a nano-channel with a first portion of the nano-channel abutting a major surface of the planar gate terminal,

wherein:

the nano-channel is configured to transport at least one charge-tagged molecule along a longitudinal axis that traverses the major surface of the planar gate terminal, and

the field-effect transistor is a carbon nanotube field effect transistor configured to undergo a change in amplitude of a source-to-drain current when the at least one charge-tagged molecule traverses the major surface of the planar gate terminal.

2. The apparatus of claim 1, wherein the nano-channel has a circular cross-section and is operative as a nanopore having a diameter selected to provide a separation distance not exceeding 2 nm between the at least one charge-tagged molecule and the major surface of the planar gate terminal.

3. The apparatus of claim 2, wherein the diameter does not exceed 3 nm.

4. The apparatus of claim 2, further comprising a graphene nanoribbon located on a major surface of the semiconductor layer with a portion of the graphene nanoribbon covering an exposed portion of the nano-channel.

5. The apparatus of claim 4, wherein the graphene nanoribbon is configured as a current detector to detect the at least one charge-tagged molecule when the at least one charge-tagged molecule traverses the major surface of the planar gate terminal.

6. The apparatus of claim 5, wherein configuring the graphene nanoribbon as the current detector comprises configuring the graphene nanoribbon to measure a sense current flowing through at least a portion of the graphene nanoribbon.

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